



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF: Tomoaki SHINO

SERIAL NUMBER: 10/767,430

GROUP: 2818

FILED: January 30, 2004

EXAMINER: HUYNH, ANDY

FOR: SEMICONDUCTOR DEVICE INCLUDING TRANSISTORS FORMED IN

SEMICONDUCTOR LAYER HAVING SINGLE-CRYSTAL STRUCTURE

ISOLATED FROM SUBSTRATE

REQUEST TO CORRECT TITLE OF INVENTION

MAIL STOP ISSUE FEE COMMISSIONER FOR PATENTS P.O. BOX 1450 ALEXANDRIA, VA 22313-1450

SIR:

In the matter of the above-identified application for patent, we hereby request correction of your records to reflect the correct title of the invention. The title of the invention should read as follows: SEMICONDUCTOR DEVICE INCLUDING TRANSISTORS FORMED IN SEMICONDUCTOR LAYER HAVING SINGLE-CRYSTAL STRUCTURE ISOLATED FROM SUBSTRATE.

Respectfully Submitted,

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